

## Supporting Information for

# Highly Enhanced Thermoelectric Performance in Halogen Elements Modified SnSe<sub>2</sub> Materials via Point Defects Engineering

Rong Li<sup>1</sup>, Chong-Yu Wang<sup>1</sup>, Qiu-Yu Luo, Ze Li, Xing Yang, Wang-Qi Bao, Yi-Xin Zhang, Jing Feng, and Zhen-Hua Ge\*.

<sup>a</sup>Faculty of Materials Science and Engineering, Kunming University of Science and Technology, Kunming, 650093, China.

<sup>b</sup>National-Local Joint Engineering Research Center for Technology of Advanced Metallic Solidification Forming and Equipment, Kunming University of Science and Technology, Kunming 650093, China.

\*Corresponding author: [zge@kust.edu.cn](mailto:zge@kust.edu.cn) (Z.-H. Ge)

The statistics of grain distribution of SnSe<sub>2</sub> samples doped with different contents of SnCl<sub>2</sub> are shown in Fig. S1.

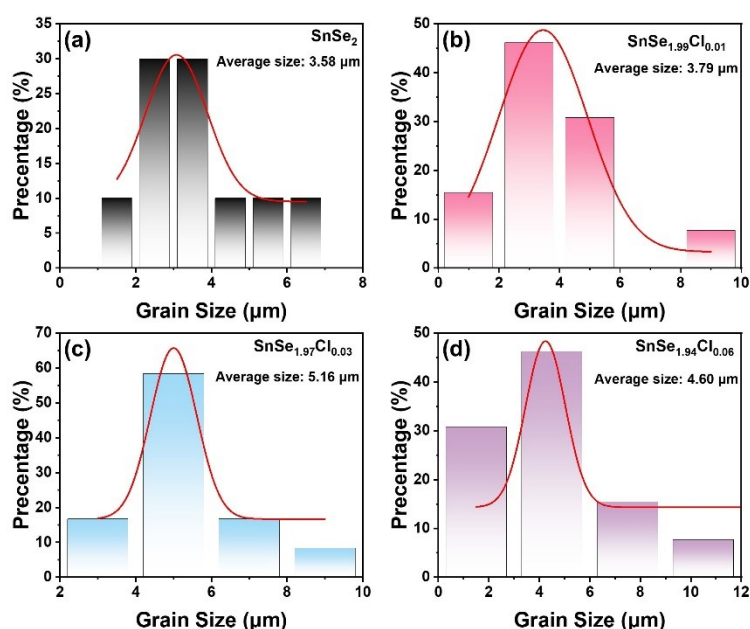


Figure S1 The grain size distributions of SnSe<sub>2-x</sub>Cl<sub>x</sub> a) x = 0, b) x = 0.01 c) x = 0.03, and d) x = 0.06 samples.